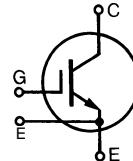


HiPerFAST™ IGBT

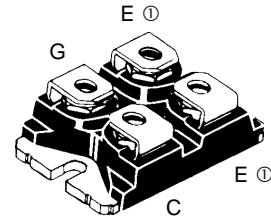
IXGN 200N60
IXGN 200N60A

V_{CES}	I_{C25}	$V_{CE(sat)}$
600 V	200 A	2.5 V
600 V	200 A	2.7 V



Symbol	Test Conditions	Maximum Ratings		
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V	
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	600	V	
V_{GES}	Continuous	± 20	V	
V_{GEM}	Transient	± 30	V	
I_{C25}	$T_c = 25^\circ\text{C}$	200	A	
I_{C90}	$T_c = 90^\circ\text{C}$	100	A	
I_{CM}	$T_c = 25^\circ\text{C}$, 1 ms	300	A	
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 22 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 100$ @ 0.8 V_{CES}	A	
P_c	$T_c = 25^\circ\text{C}$	600	W	
T_J		-55 ... +150	$^\circ\text{C}$	
T_{JM}		150	$^\circ\text{C}$	
T_{stg}		-55 ... +150	$^\circ\text{C}$	
V_{ISOL}	50/60 Hz $I_{ISOL} \leq 1 \text{ mA}$	t = 1 min t = 1 s	2500 3000	V_{\sim}
M_d	Mounting torque Terminal connection torque (M4)	1.5/13	Nm/lb.in. Nm/lb.in.	
Weight		30	g	

SOT-227B, miniBLOC



G = Gate, C = Collector, E = Emitter

① either emitter terminal can be used as Main or Kelvin Emitter

Features

- International standard package miniBLOC (ISOTOP compatible)
- Aluminium nitride isolation
 - high power dissipation
- Isolation voltage 3000 V \sim
- Very high current, fast switching IGBT
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- MOS Gate turn-on
 - drive simplicity
- Low collector-to-case capacitance (< 50 pF)
- Low package inductance (< 5 nH)
 - easy to drive and to protect

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

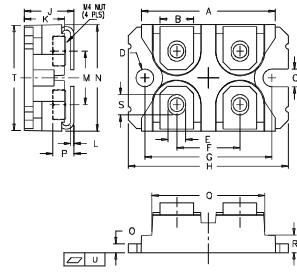
Advantages

- Easy to mount with 2 screws
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
BV_{CES}	$I_c = 250 \mu\text{A}$, $V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_c = 10 \text{ mA}$, $V_{CE} = V_{GE}$	2.5	6	V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	200 2	μA mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$		± 400	nA
$V_{CE(sat)}$	$I_c = I_{C90}$, $V_{GE} = 15 \text{ V}$	200N60 200N60A	2.5 2.7	V

Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
g_{fs}	$I_C = 60 \text{ A}; V_{CE} = 10 \text{ V},$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$	40	57	S
C_{ies}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	9000	pF	
C_{oes}		600	pF	
C_{res}		305	pF	
Q_g	$I_C = I_{C90}, V_{GE} = 15 \text{ V}, V_{CE} = 0.5 V_{CES}$	465	nC	
Q_{ge}		52	nC	
Q_{gc}		228	nC	
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15 \text{ V}, L = 30 \mu\text{H},$ $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 2.4 \Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G	100	ns	
t_{ri}		100	ns	
E_{on}		2.4	mJ	
$t_{d(off)}$		200N60	800	1100 ns
t_{fi}		200N60A	700	950 ns
E_{off}		200N60	350	500 ns
		200N60A	200	280 ns
		200N60	14.4	mJ
		200N60A	9.6	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ (IXGN 200N60A) $I_C = I_{C90}, V_{GE} = 15 \text{ V}, L = 30 \mu\text{H}$ $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 2.4 \Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G	100	ns	
t_{ri}		200	ns	
E_{on}		4.8	mJ	
$t_{d(off)}$		780	ns	
t_{fi}		250	ns	
E_{off}		14.4	mJ	
R_{thJC}			0.21	K/W
R_{thCK}		0.05		K/W

miniBLOC, SOT-227 B



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

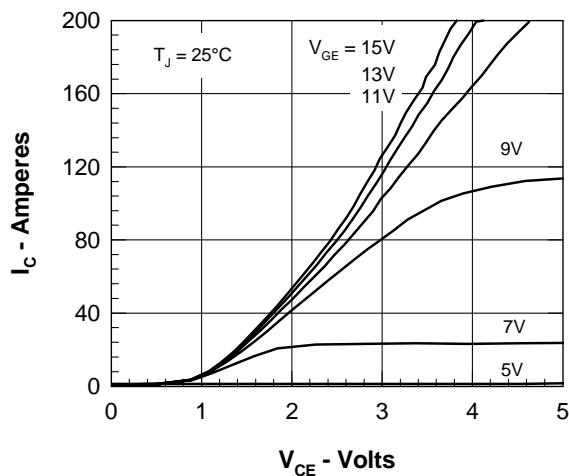


Fig. 1. Saturation Voltage Characteristics

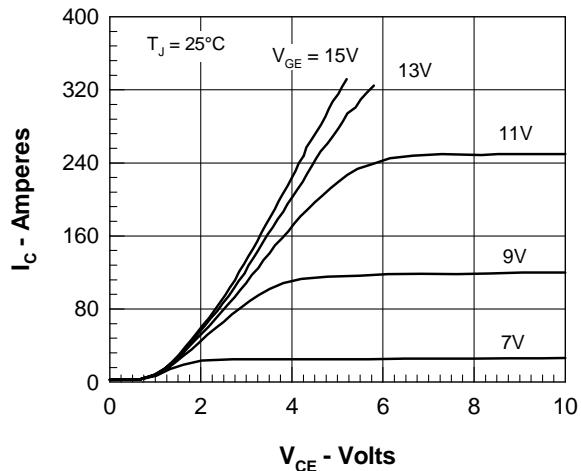


Fig. 2. Extended Output Characteristics

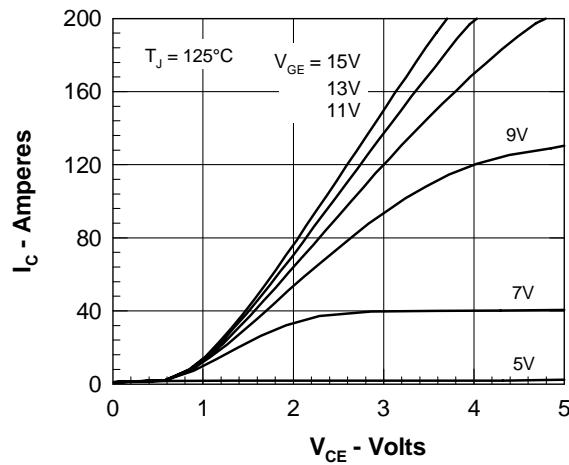


Fig. 3. Saturation Voltage Characteristics

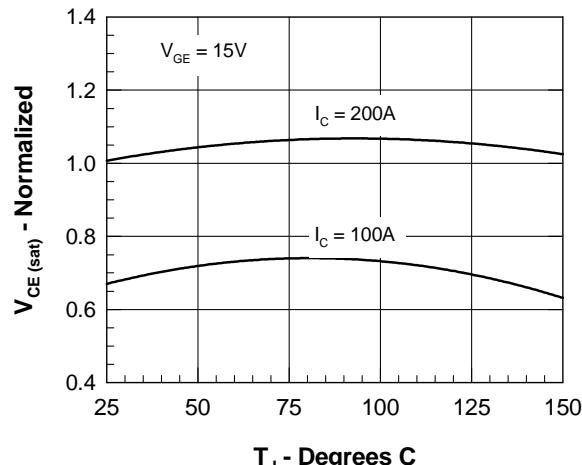
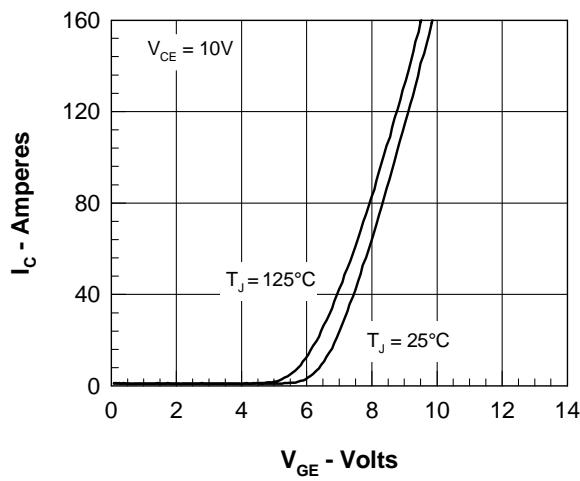
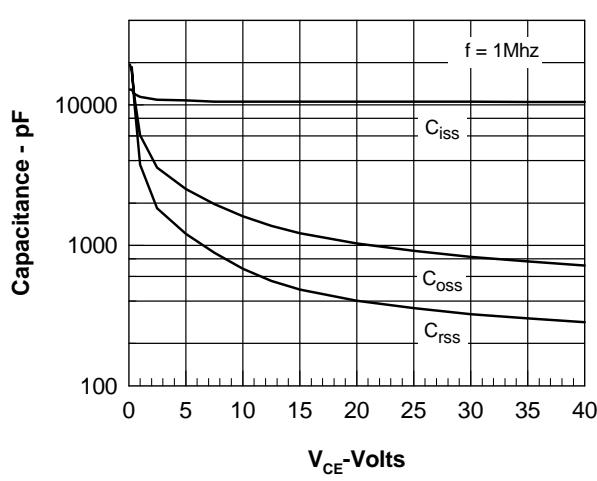
Fig. 4. Temperature Dependence of $V_{CE(sat)}$ 

Fig. 5. Turn-off Safe Operating Area

Fig. 6. Temperature Dependence of BV_{CES} & $V_{GE(th)}$

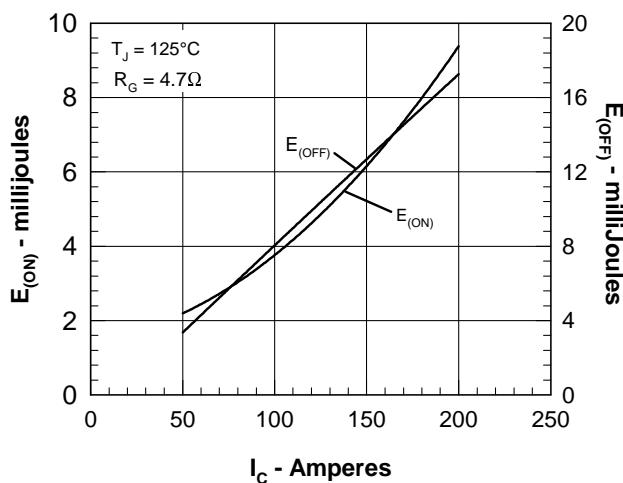
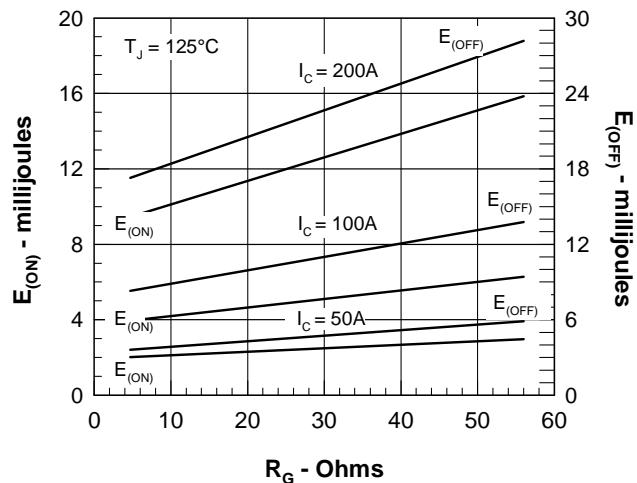
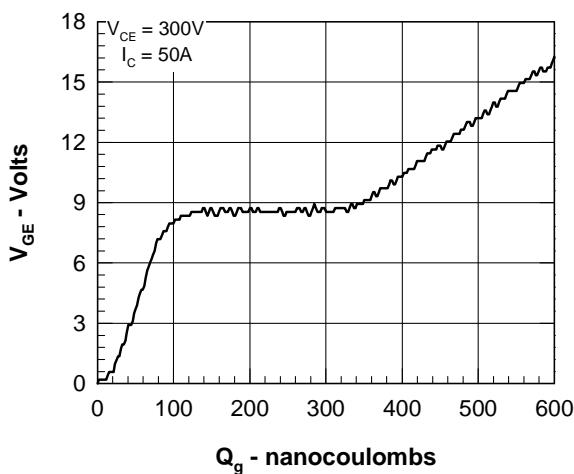
Fig. 7. Dependence of t_{fi} and E_{OFF} on I_C.Fig. 8. Dependence of t_{fi} and E_{OFF} on R_G.

Fig. 9. Gate Charge

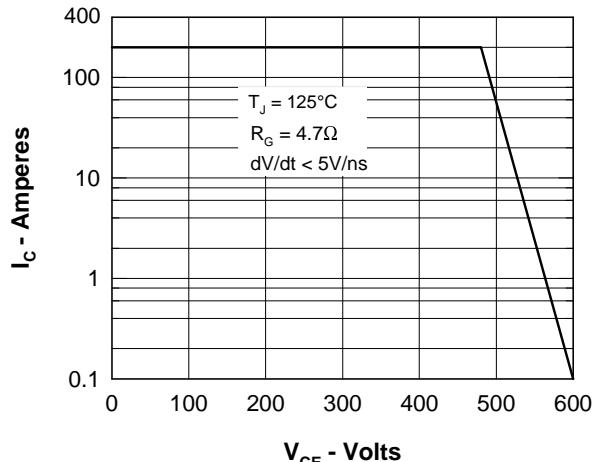


Fig. 10. Junction Capacitance Curves

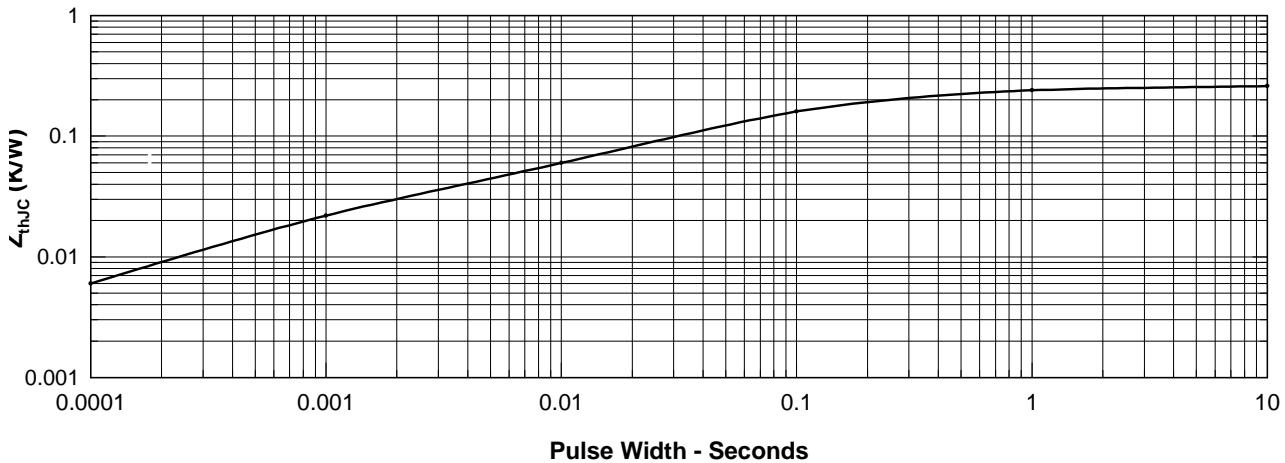


Fig. 11. Transient Thermal Resistance